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SAMSUNG ELECTRONICS CO., LTD.
Petitioner

v.

DSS TECHNOLOGY MANAGEMENT, INC.
Patent Owner

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Case IPR. No. **Unassigned**
U.S. Patent No. 6,784,552
Title: STRUCTURE HAVING REDUCED LATERAL SPACER EROSION

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# Petition For *Inter Partes* Review of U.S. Patent No. 6,784,552 Under 35 U.S.C. §§ 311-319 and 37 C.F.R. §§ 42.1-.80, 42.100-.123

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